

can be adjusted independently of one another.

79. (New) The plasma CVD device according to claim 78, wherein:  
the plasma CVD device is operated as a pass-through arrangement  
in which the substrate is moved on one of a uniform fashion and a pulsed  
fashion.

80. (New) The plasma CVD device according to claim 78, wherein:  
the arrangement for producing the plasma is operated in a pulsed  
fashion.

81. (New) A multilayer structure, comprising:  
alternating individual hard-material layers and one of individual carbon layers  
and individual silicon layers, wherein:

the hard-material layers include one of a metal, a metal carbide, a  
metal silicide, a metal carbo-silicide, a metal siliconitride, a metal carbide-  
containing carbon, a metal silicide-containing silicon, and a mixture of at least  
two of the metal, the metal carbide, the metal silicide, the metal carbo-silicide,  
the metal siliconitride, the metal carbide-containing carbon, and the metal  
silicide-containing silicon, and

the metal includes one of tungsten, chromium, niobium, and  
molybdenum.

82. (New) The multilayer structure according to claim 81, wherein:  
the carbon layers include one of amorphous carbon containing  
hydrogen, amorphous hydrogen-free carbon, carbon containing silicon, and  
carbon containing the metal, and  
the metal is selected from hard subgroup metals.

83. (New) The multilayer structure according to claim 81, wherein:

the silicon layers include one of amorphous silicon containing hydrogen, amorphous hydrogen-free silicon, silicon containing carbon, and silicon containing metal.

84. (New) The multilayer structure according to claim 81, wherein:  
the hard material layers include at least one type of hard material layer,  
the carbon layers include at least one type of carbon layer, and  
the silicon layers include at least one type of silicon layer.

85. (New) The multilayer structure according to claim 84, wherein:  
the hard material layers include one type of hard material layer,  
the carbon layers include one type of carbon layer, and  
the silicon layers include one type of silicon layer.

86. (New) The multilayer structure according to claim 81, wherein:  
thicknesses of the hard material layers, the silicon layers, and the carbon layers are between approximately 1 nm and approximately 10 nm.

87. (New) The multilayer structure according to claim 81, wherein:  
thicknesses of the hard material layers, the silicon layers, and the carbon layers are between approximately 2 nm and approximately 5 nm.

88. (New) The multilayer structure according to claim 81, wherein:  
an overall layer thickness of the multilayer structure is between approximately 1  $\mu\text{m}$  and approximately 10  $\mu\text{m}$ .

89. (New) The multilayer structure according to claim 81, wherein:  
an overall layer thickness of the multilayer structure is between approximately 1  $\mu\text{m}$  and approximately 4  $\mu\text{m}$ .

90. (New) The multilayer structure according to claim 81, wherein:  
the hard material layers include one of Me, MeC, MeSi, Me(CSi),  
and Me(SiN),  
and  
the carbon layers include one of a-C:H and a-C.
91. (New) The multilayer structure according to claim 81, wherein:  
the multilayer structure is made up of alternating C-(WC) layers and  
a-C:H layers.
92. (New) The multilayer structure according to claim 81, wherein:  
the multilayer structure is made up of alternating MeC layers and C-  
(MeC) layers.
93. (New) The multilayer structure according to claim 81, wherein:  
the hard material layers include one of Me, MeC, MeN, MeSi,  
Me(CN), Me(CSi), and Me(SiN), and  
the silicon layers include one of a-Si:H or a-Si.
94. (New) The multilayer structure according to claim 81, wherein:  
one of the hard material layers, the carbon layers, and the silicon  
layers contain at least one of silicon, boron, nitrogen, oxygen, carbon, and a  
metal, and  
boron and carbon are not simultaneously present in the one of the  
hard material layers, the carbon layers, and the silicon layers.
95. (New) The multilayer structure according to claim 81, wherein:  
the multilayer structure is capable of coating one of a machining  
tool and a non-cutting shaping tool.)
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